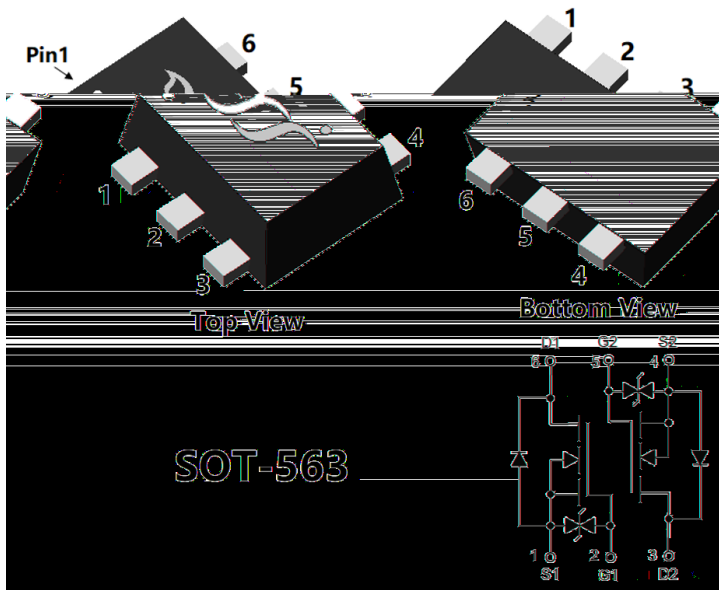


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	20 V
I_D	0.5 A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<300 mohm
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	<400 mohm
$R_{DS(ON)}$ (at $V_{GS}=1.8V$)	<950 mohm
ESD Protected Up to 2.0KV (HBM)	

General Description

Trench Power LV MOSFET technology
High Power and current handling capability

Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

PWM application
Load switch

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	20	V
Gate-source Voltage	V_{GS}	± 10	V
Drain Current	I_D	$T_A=25^\circ C$ @ Steady State	0.5
		$T_A=70^\circ C$ @ Steady State	0.4
Pulsed Drain Current ^A	I_{DM}	3.3	A
Total Power Dissipation @ $T_A=25^\circ C$	P_D	0.18	W
Thermal Resistance Junction-to-Ambient @ Steady State	R_{JA}	694	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

Ordering Information

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3134KBX	F2	34B	3000	30000	120000	reel



YJL3134KBX

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±10V, V _{DS} =0V		2.5	±10	
		V _{GS} = ±8V, V _{DS} =0V		500	±2000	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250	0.35	0.75	1.1	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =0.5A		220	300	
		V _{GS} =2.5V, I _D =0.45A		290	400	
		V _{GS} =1.8V, I _D =0.2A		420	950	
Diode Forward Voltage ^C	V _{SD}	I _S =0.5A, V _{GS} =0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I _S				0.5	A
Gate Resistance	R _g	f=1 MHz, Open drain		50		Ω
Dynamic Parameters^B						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz		33		pF
Output Capacitance	C _{oss}			20		
Reverse Transfer Capacitance	C _{rss}			10		
Switching Parameters^B						
Total Gate Charge	Q _g	V _{GS} =4.5V, V _{DS} =10V, I _D =0.5A		0.8		nC
Gate Source Charge	Q _{gs}			0.3		
Gate Drain Charge	Q _{gd}			0.15		
Reverse Recovery Charge	Q _{rr}	I _F =0.5A, di/dt=20A/us		0.4		
Reverse Recovery Time	t _{rr}			14.4		
Turn-on Delay Time	t _{D(on)}	V _{GS} =4.5V, V _{DD} =10V, R _G =10Ω, I _D =500mA		4		ns
Turn-on Rise Time	t _r			18.8		
Turn-off Delay Time	t _{D(off)}			10		
Turn-off Fall Time	t _f			23		

A. Repetitive Rating: Pulse width limited by maximum junction temperature.

B. These parameters have no way to verify.

C.



■ Typical Performance Characteristics

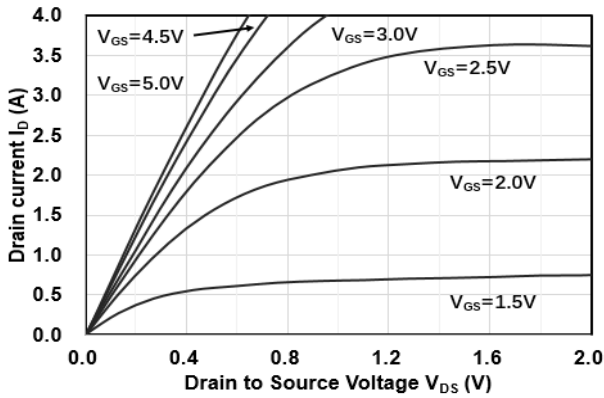


Figure1. Output Characteristics

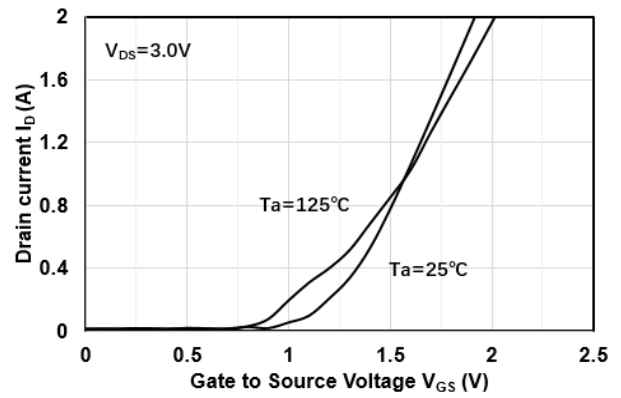


Figure2. Transfer Characteristics

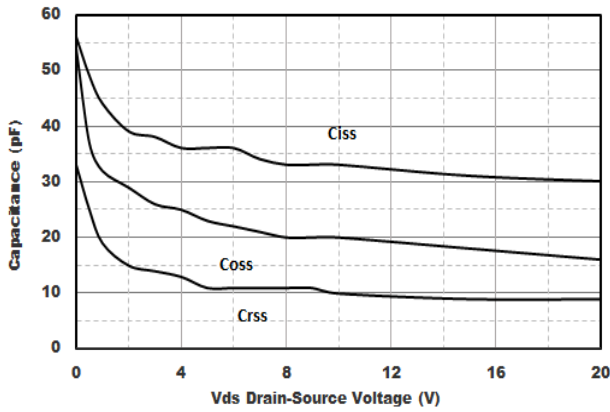


Figure3. Capacitance Characteristics

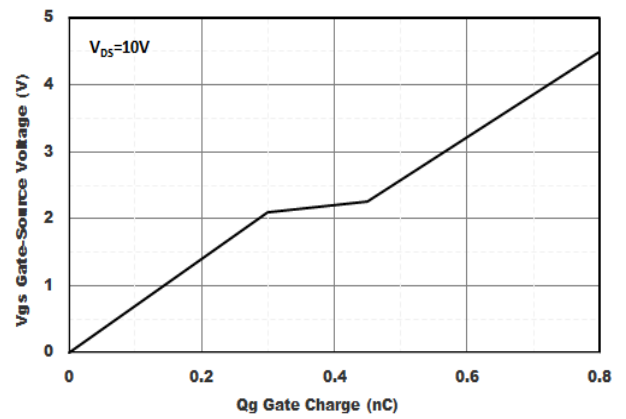


Figure4. Gate Charge

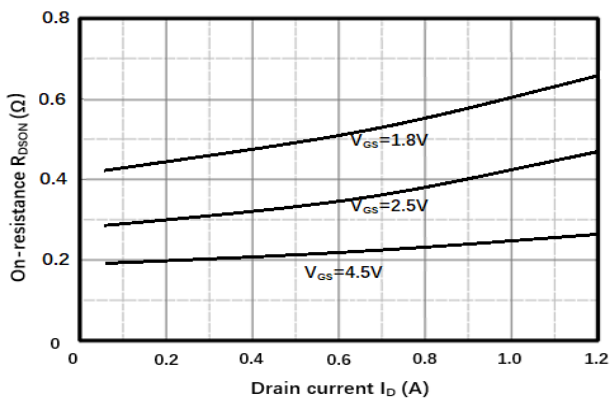


Figure5. Drain-Source on Resistance

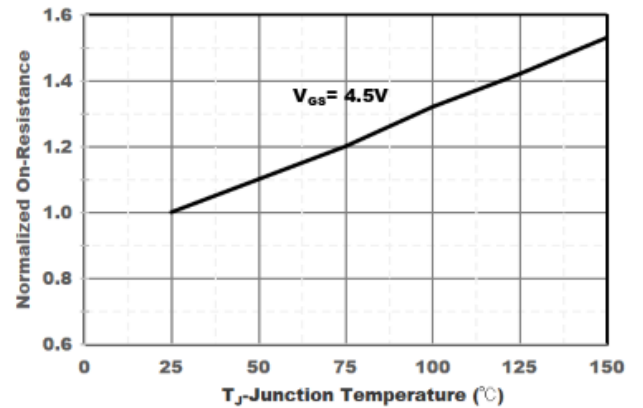


Figure6. Drain-Source on Resistance



YJL3134KBX

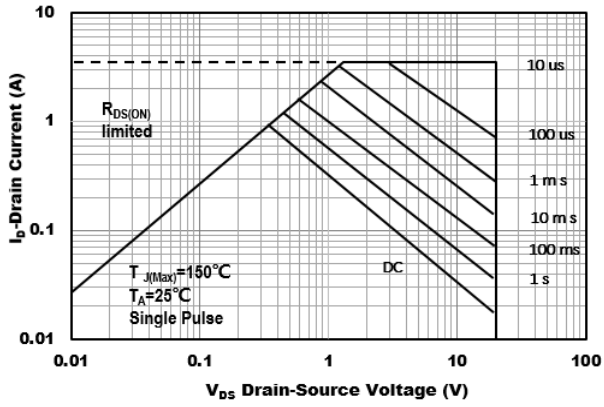


Figure7. Safe Operation Area

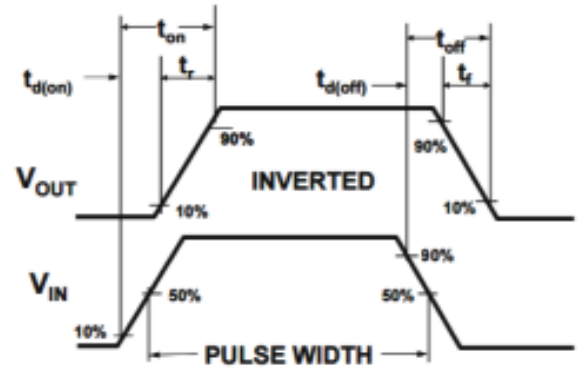
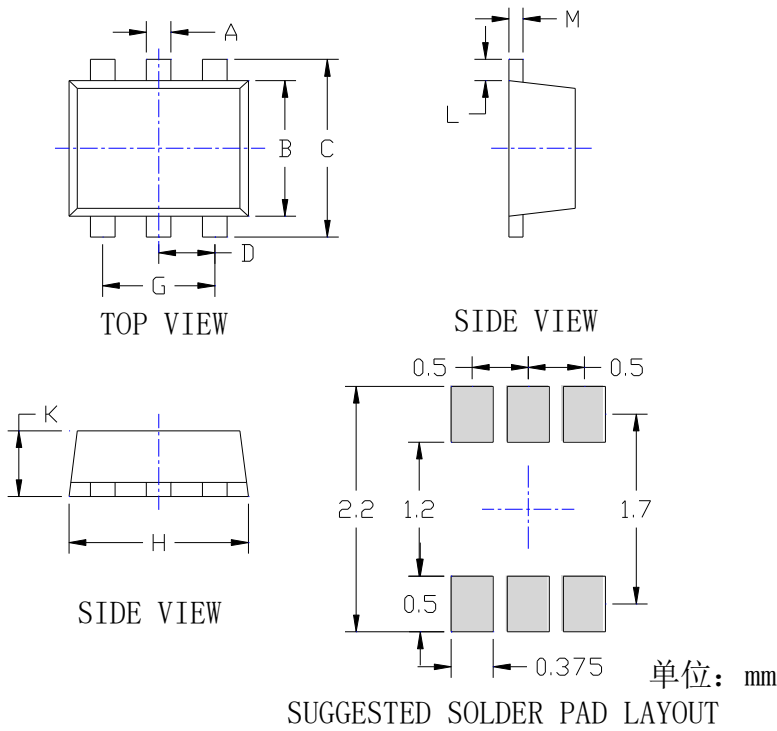


Figure8. Switching wave



YJL3134KBX

SOT-563 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.006	0.011	0.150	0.300
B	0.043	0.051	1.100	1.300
C	0.059	0.067	1.500	1.700
D	0.016	0.024	0.400	0.600
G	0.035	0.043	0.900	1.100
H	0.059	0.067	1.500	1.700
K	0.021	0.026	0.550	0.650
L	0.004	0.011	0.100	0.300
M	0.004	0.007	0.100	0.180

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

